+ I G 8J 9I@ 8 8 K PI@KFI

FN =FIN8I MF08

@ N8M JLI @ : 8G89@@

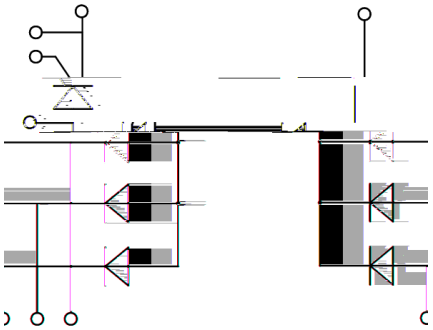
-))		-
K DJ		
- 8O		-

M IK I =FI FI DFKFI : F KFC

LII KJK89@@ GFN I JLGGP

N@ @ GFN I JLGGP





+ L CJJ FK IN@ JG : @@

) G K@ G 8BI M IJ MF08		-)))		-
F I G K@ G 8BI M IJ MF08	+MA	-)		-
I@ FLKGLK: LII K	+	D(-)		
) G K@ G 8B=FIN8I : LII K	K DJ +MA	+		
KM8C =FI =LJ@	K DJ +MA	K		J
I@8CI8K F=I@ F=F JK8K : LII K		@K		J
I@8CI8K F=I@ F=MF08	- -) + ℃ 8K G	M K		- J

+ L CJJ FK IN@ JG : @@

FIN8I MF@8	+	- +				-
) GK@@ G 8BF=JK8K : LII K	- -) +MA ℃	)				D
	- -) +MA ℃					D
) MIJ C8B8 : LII K	-) -)) +MA ℃	))				D
	-) -)) +MA ℃					D
+ I J FC MF@8	FI GFN I CJJ : 8CL@K@ F C+MA ℃	- +				-
P 8D@I J@K8 :	+MA ℃	I+				D
+I@ I@ 8K MF@8	- -)	- +				-
+I@ I@ 8K : LII K	- -)	+				D
FC@ : LII K	+					D
8K @ : LII K	+					D
F K@ I@ 8K MF@8	- -) , +MA ℃	-				-
+ ID8CI J@K8 : A : K@ KF :8J	GI @	) K				.
+ DGI8KLI L IFGI8K@ :F @@ J		+-A				℃

+ L CJJ FK IN@ JG : @@

) GK@@ G 8BI MIJ MF@8		-))		-
F I GK@@ G 8BI MIJ MF@8		-)		-
LKGLK: LII K	+ ℃			
FIN8I JLI : LII K	: P. C @ N8M Q +MA ℃			
KMBCL =FI=LJ@		K		J
+ DGI8KLI L IFGI8K@ :F @@ J		+-A		℃

+ L CJJ FK IN@ JG : @@

FIN8I MF@8	+MA ℃	-				-
) MIJ C8B8 : LII K	-) -)) +MA ℃	))				D
	-) -)) +MA ℃					D
+ ID8CI J@K8 : A. : K@ KF : 8J	G I @	) K				.

+ L CJJ FK IN@ JG : @@

) @F8KH@ MF@8	Q. D@	-				-
+ ID8CI J@K8 : : 8J KF 8KJ@B	G I DF LC	) K				.
8O@LD L : K@ + DG I8KLI	+ PI@KFI	+MAD8O				℃
	@					℃
KFI8 KDG I8KLI I8		+JK				℃
FL K@ KFIHL	+F K ID@8CI	K				D
	+F 8KJ@BJ	J				D

+ +

FIG.7: Forward characteristics(per diode)

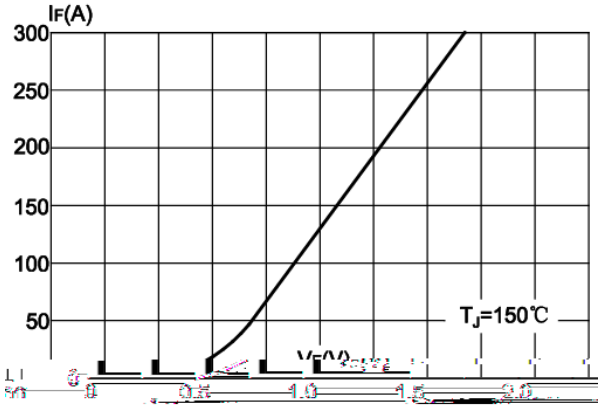
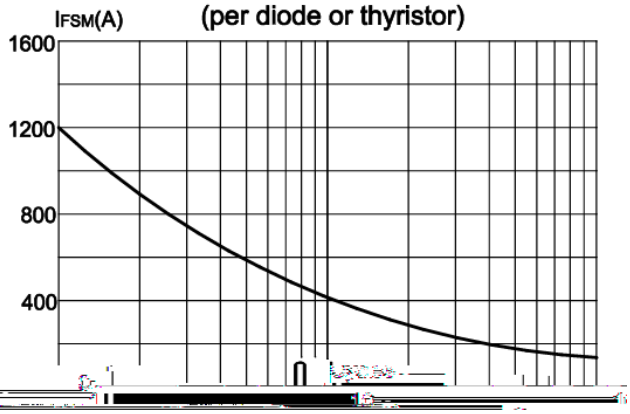


FIG.8: Peak on-state surge current (per diode or thyristor)



ıximum transient thermal impedance Junction-to-case(per diode)

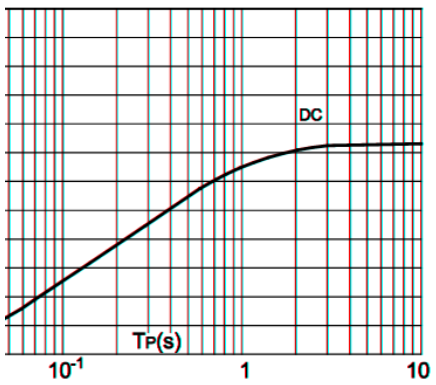


FIG.9: Forward current vs. case temperature (per diode)

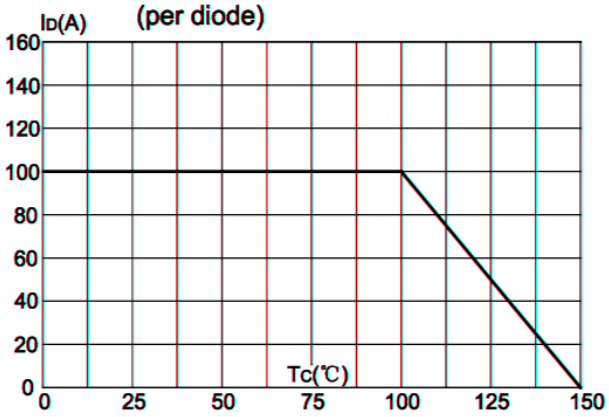
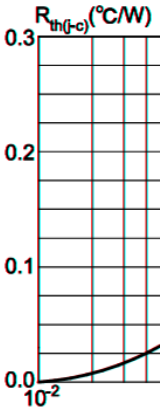
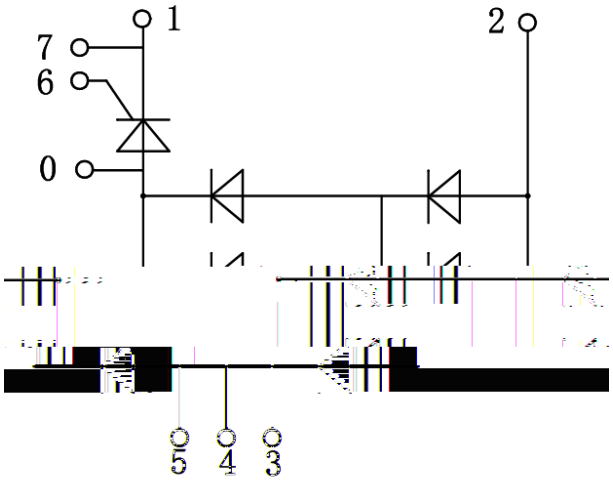
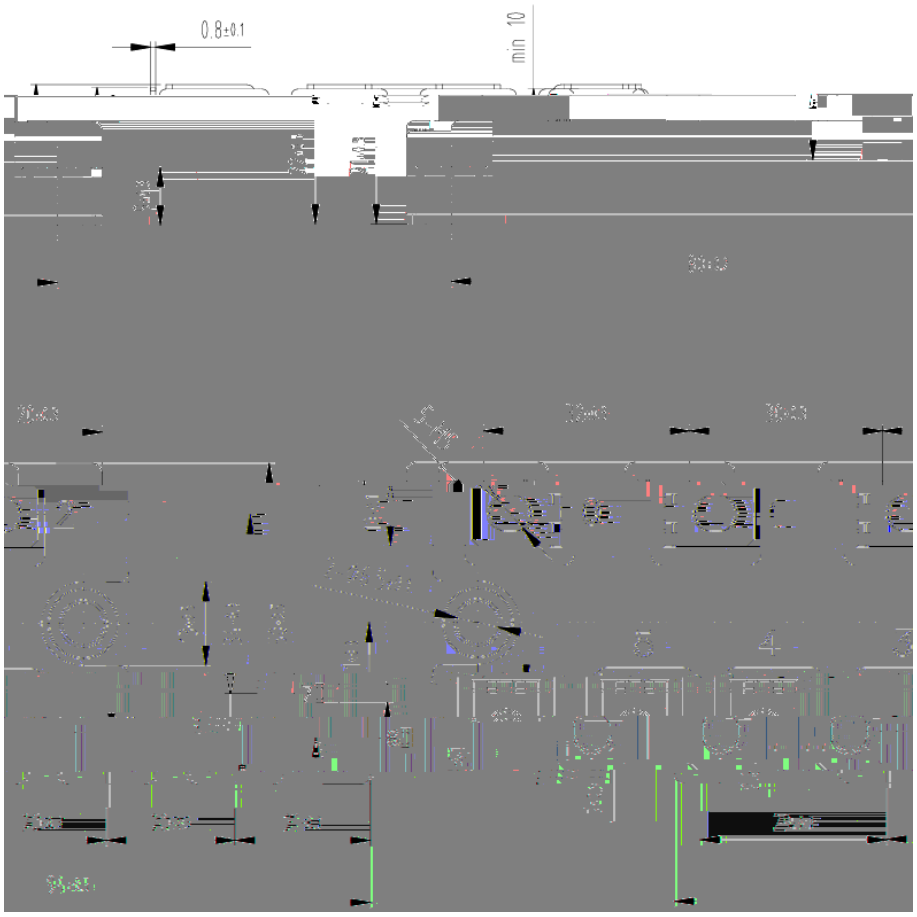


FIG.10: Ma







, @F=D 8JLI D KDD